

NVMTS2003 PROGRAM

WEDNESDAY Nov 12	
Introduction & Welcoming Remarks	
	NVMTS2002 Best Presentation Award Recipient: Michelle Bell <i>Radiant Technologies</i>
[1]	Keynote Address: Difficult Predictions: Future OSS Goals and IT/IS Investments Dr. Harley Thronson Director of Technology, Office of Space Science, NASA
[2]	Invited Talk: Non-Volatile Memory Technology Programs at the Defense Threat Reduction Agency Radiation Hardened Microelectronics Project; <i>by L. Cohn, DTRA</i>
[3]	Applications R. Katti Honeywell Solid State Electronics Center, Chair
	Radiation Effects on Microelectronics and Future Space Missions; <i>by J. Patterson, JPL</i>
[4]	Non-Volatile Memory With A Mission; <i>by R. Sinclair, NVE</i>
[5]	Scaled SONOS NVSM Devices for Space and Military Applications; <i>by M. White, et al, Lehigh Univ.</i>
[6]	Case Study: A Commercially Fabricated 256K RadHard ViaLink® PROM; <i>by B. Baranski and A. Jordan, Aeroflex</i>
[7]	Invited Talk: Non-Volatile Memory Needs for Air Force Space Systems and Approaches to Radiation Harden Non-Volatile Memories by the Application of Design Techniques, R. LaCoe, <i>et al, Aerospace Corporation</i>
[8]	Processing & Modeling G. Derbenwick, Celis Semiconductor, Chair
	Hardened by Design Ferroelectric Memories for Space Applications; <i>by S. Philpy, et al, Celis Semiconductor</i>
[9]	Demonstration Of A 4 Mb High Density, Embedded Ferroelectric Memory Technology; <i>by S. Gilbert, Agilent Laboratories</i>
[10]	High-Speed 128Kbit MRAM Core in a 0.18µm CMOS Technology Utilizing PtMn-based Magnetic Tunnel Junctions; <i>by W. Gallagher and S. Parker, IBM</i>
[11]	Stabilization of Magnetism in Ferromagnetic Dot Arrays Towards Terabit per Square Inch Storage; <i>by I. Roshchin, et al, University of California at San Diego</i>
[12]	Biased Target Ion Beam Deposition of GMR Multilayers; <i>by H. Wadley, et al, University of Virginia</i>
[13]	Non Volatile Memory Cell Design : Sizing Assisted By A Predictive Model; <i>by P. Canet, et al, L2MP</i>
L1	LATE PAPER: Honeywell Radiation Hardened Non-Volatile Memory (MRAM) Product Development; <i>by R. Katti, Honeywell SSEC</i>

THURSDAY Nov 13	
Reconvening Remarks	
[14]	Invited Talk: Ballistic Magnetoresistance in Ferromagnetic Nanocontacts; <i>by H-D Chopra, et al, SUNY/Buffalo</i>
[15]	INNOVATIVE CONCEPTS J Zhu Carnegie-Mellon University, Chair
	Invited Paper: SpinRAM, A 1Gbit Nonvolatile Memory; <i>by R Spitzer, IME</i>
[L2]	LATE PAPER Hewlett-Packard's Atomic Resolution Storage (ARS) Program; <i>by K. Eldredge, HP Boise</i>
[16]	A Low Power Vertical MRAM; <i>by X. Zhu and J. Zhu, Carnegie Mellon University</i>
[17]	Electrical Characterization of Solid State Ionic Memory Elements; <i>by R. Symanczyk, et al, Infineon</i>
[18]	Fabrication and Properties of Electrical Pulse Induced Resistive Memory; <i>by N. Wu, et al, University of Houston</i>
[19]	Holographic Memory Using MEMS Mirror Beam Steering Technology; <i>by T-H Chao, et al, JPL</i>
[20]	Test Ken Hunt AFRL Chair
	Endurance cycling in extreme environments; <i>by S. Guertin, JPL</i>
[21]	TID, SEE and Radiation Induced Failures in Advanced Flash Memories; <i>by D. Nguyen, JPL</i>
[22]	Chalcogenide Random Access Memory Technology Status; <i>by J. Maimon, et al, BAE</i>
[23]	SuperFlash® Memory Program/Erase Endurance ; <i>by A.Kotov, et al, SST Corporation</i>
[24]	Characterization of Nonvolatile Transistors; <i>by J. Evans, Radiant Technologies</i>
[25]	SPECIAL PANEL SESSION Packaging Technologies MCP and SiP, R. Andrei, Web-Feet Research, Chair
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